

TOSHIBA

TLP521-1, TLP521-2, TLP521-4

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

TLP521-1, TLP521-2, TLP521-4

PROGRAMMABLE CONTROLLERS

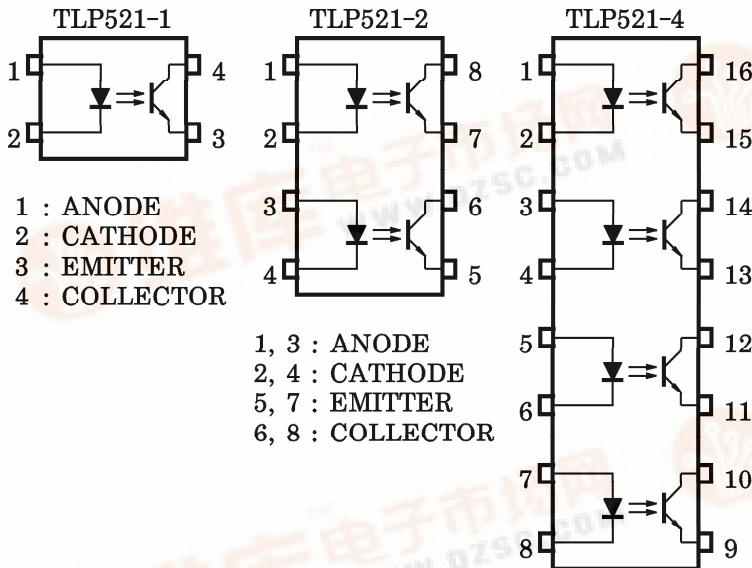
AC/DC-INPUT MODULE

SOLID STATE RELAY

The TOSHIBA TLP521-1, -2 and -4 consist of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode. The TLP521-2 offers two isolated channels in an eight lead plastic DIP package, while the TLP521-4 provides four isolated channels in a sixteen plastic DIP package.

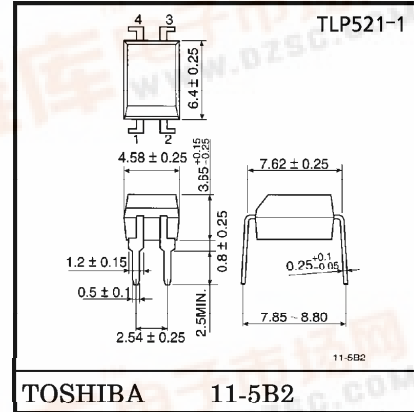
- Collector-Emitter Voltage : 55V (Min.)
- Current Transfer Ratio : 50% (Min.)
- Rank GB : 100% (Min.)
- Isolation Voltage : 2500Vrms (Min.)
- UL Recognized
 - made in Japan : UL1577, File No. E67349
 - made in Thailand : UL1577, File No. E152349

PIN CONFIGURATIONS (TOP VIEW)



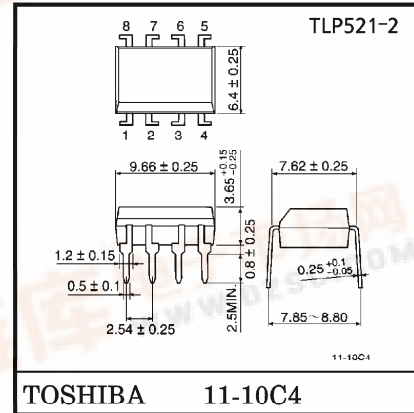
- 1, 3, 5, 7 : ANODE
- 2, 4, 6, 8 : CATHODE
- 9, 11, 13, 15 : EMITTER
- 10, 12, 14, 16 : COLLECTOR

Unit in mm



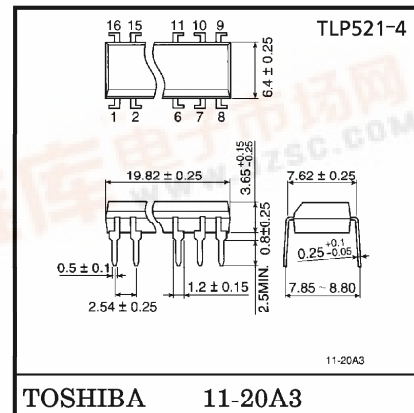
TOSHIBA 11-5B2

Weight : 0.26g



TOSHIBA 11-10C4

Weight : 0.54g



TOSHIBA 11-20A3

Weight : 1.1g

961001EBC2



MAXIMUM RATINGS (Ta = 25°C)

	CHARACTERISTIC	SYMBOL	RATING		UNIT
			TLP521-1	TLP521-2 TLP521-4	
LED	Forward Current	I_F	70	50	mA
	Forward Current Derating	$\Delta I_F / ^\circ C$	-0.93 (Ta \geq 50°C)	-0.5 (Ta \geq 25°C)	mA / °C
	Pulse Forward Current	I_{FP}	1 (100 μ pulse, 100pps)		A
	Reverse Voltage	V_R	5		V
	Junction Temperature	T_j	125		°C
DETECTOR	Collector-Emitter Voltage	V_{CEO}	55		V
	Emitter-Collector Voltage	V_{ECO}	7		V
	Collector Current	I_C	50		mA
	Collector Power Dissipation (1 Circuit)	P_C	150	100	mW
	Collector Power Dissipation Derating (1 Circuit, Ta \geq 25°C)	$\Delta P_C / ^\circ C$	-1.5	-1.0	mW / °C
	Junction Temperature	T_j	125		°C
Storage Temperature Range	T_{stg}	-55~125		°C	
Operating Temperature Range	T_{opr}	-55~100		°C	
Lead Soldering Temperature	T_{sol}	260 (10 sec.)		°C	
Total Package Power Dissipation	P_T	250	150	mW	
Total Package Power Dissipation Derating (Ta \geq 25°C)	$\Delta P_T / ^\circ C$	-2.5	-1.5	mW / °C	
Isolation Voltage	BV_S	2500 (AC, 1 min., R.H. \leq 60%) (Note 1)		Vrms	

(Note 1) Device considered a two terminal device : LED side pins shorted together and DETECTOR side pins shorted together.

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V_{CC}	—	5	24	V
Forward Current	I_F	—	16	20	mA
Collector Current	I_C	—	1	10	mA
Operating Temperature	T_{opr}	-25	—	85	°C

● Gallium arsenide (GaAs) is a substance used in the products described in this document. GaAs dust and fumes are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them. When disposing of the products, follow the appropriate regulations. Do not dispose of the products with other industrial waste or with domestic garbage.
 ● The products described in this document are subject to foreign exchange and foreign trade control laws.
 ● The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
 ● The information contained herein is subject to change without notice.

TYPE	CLASSIFICATION (*1)	CURRENT TRANSFER RATIO (%) (I_C / I_F)		MARKING OF CLASSIFICATION
		$I_F = 5\text{mA}, V_{CE} = 5\text{V}, T_a = 25^\circ\text{C}$		
		MIN.	MAX.	
TLP521	A	50	600	BLANK, Y, Y [■] , G, G [■] , B, B [■] , GB
	Rank Y	50	150	Y, Y [■]
	Rank GR	100	300	G, G [■]
	Rank BL	200	600	B, B [■]
	Rank GB	100	600	G, G [■] , B, B [■] , GB
TLP521-2	A	50	600	BLANK, GR, BL, GB
TLP521-4	Rank GB	100	600	GR, BL, GB

*1 : Ex. Rank GB : TLP521-1 (GB)

(Note) Application type name for certification test, please use standard product type name, i.e.

TLP521-1 (GB) : TLP521-1, TLP521-2 (GB) : TLP521-2

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V_F	$I_F = 10\text{mA}$	1.0	1.15	1.3	V
	Reverse Current	I_R	$V_R = 5\text{V}$	—	—	10	μA
	Capacitance	C_T	$V = 0, f = 1\text{MHz}$	—	30	—	pF
DETECTOR	Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 0.5\text{mA}$	55	—	—	V
	Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	$I_E = 0.1\text{mA}$	7	—	—	V
	Collector Dark Current	I_{CEO}	$V_{CE} = 24\text{V}$	—	10	100	nA
			$V_{CE} = 24\text{V}, T_a = 85^\circ\text{C}$	—	2	50	μA
Capacitance (Collector to Emitter)	C_{CE}	$V = 0, f = 1\text{MHz}$	—	10	—	pF	

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	I_C / I_F	$I_F = 5\text{mA}, V_{CE} = 5\text{V}$ Rank GB	50	—	600	%
			100	—	600	
Saturated CTR	$I_C / I_{F(sat)}$	$I_F = 1\text{mA}, V_{CE} = 0.4\text{V}$ Rank GB	—	60	—	%
			30	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 2.4\text{mA}, I_F = 8\text{mA}$ $I_C = 0.2\text{mA}, I_F = 1\text{mA}$ Rank GB	—	—	0.4	V
			—	0.2	—	
			—	—	0.4	

ISOLATION CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance (Input to Output)	C_S	$V_S = 0, f = 1\text{MHz}$	—	0.8	—	pF
Isolation Resistance	R_S	$V_S = 500\text{V}, R.H. \leq 60\%$	—	10^{11}	—	Ω
Isolation Voltage	BV_S	AC, 1 minute	2500	—	—	V_{rms}
		AC, 1 second, in oil	—	5000	—	
		DC, 1 minute, in oil	—	5000	—	Vdc

SWITCHING CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	t_r	$V_{CC} = 10V$ $I_C = 2mA$ $R_L = 100\Omega$	—	2	—	μs
Fall Time	t_f		—	3	—	
Turn-on Time	t_{on}		—	3	—	
Turn-off Time	t_{off}		—	3	—	
Turn-on Time	t_{ON}	$R_L = 1.9k\Omega$ (Fig.1) $V_{CC} = 5V, I_F = 16mA$	—	2	—	μs
Storage Time	t_s		—	15	—	
Turn-off Time	t_{OFF}		—	25	—	

Fig.1 SWITCHING TIME TEST CIRCUIT

